

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

IRFI1010N

FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- · Low gate input resistance
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching applications

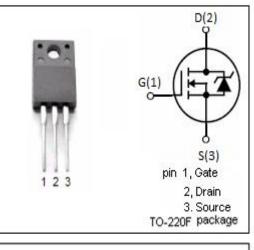
ABSOLUTE MAXIMOM (ATINGS(Ta=23 C)						
SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	55	V			
V _{GSS}	Gate-Source Voltage	±20	V			
Ι _D	Drain Current-Continuous @Tc=25℃ (V _{GS} at 10V) Tc=100℃	49 35	А			
I _{DM}	Drain Current-Single Pulsed	290	A			
PD	Total Dissipation @Tc=25°C	58	W			
Tj	Max. Operating Junction Temperature 175		°C			
T _{stg}	Storage Temperature	-55~175	°C			

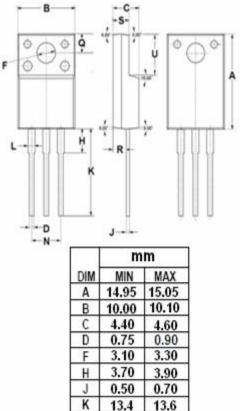
• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	2.6	°C /W	
Rth(ch-a)	n(ch-a) Channel-to-ambient thermal resistance		°C/W	

1





1.10

5.00

2.70

2.20

6.40

N

Q

R

5

1.30

5.20

2.90

2.40

2.90

6.60

isc website: www.iscsemi.cn



Isc N-Channel MOSFET Transistor

IRFI1010N

ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	55			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.25mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =26A			12	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 55V; V _{GS} = 0V;Tj=25℃ V _{DS} = 55V; V _{GS} = 0V; Tj=150℃			25 250	μA
V _{SDF}	Diode forward voltage	I_{SD} =26A, V_{GS} = 0 V			1.3	V

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

2